

- Species 2 - embodiments of Figs. 3, 4a-4e and 6a-6e, involving forming a SOI FET having lattice defect regions (or, heavily doped regions) disposed under both of the entire source/drain regions and the entire channel region, and having sidewall spacers but without silicide layers; and
- Species 3 - embodiments of Figs. 7a-7e, 9 and 10a-10e, involving forming a SOI FET having lattice defect regions (or, heavily doped regions) disposed only in the channel bottom corners with the silicide layers as a doping mask, after the sidewall spacers are removed.

In response to the foregoing restriction, Applicants elect **Species 2, embodiments of Figs. 3, 4a-4e and 6a-6e**, and identify claims 16-23 as reading on the elected Species.

Applicants also reserve the right to file a Divisional Application for the non-elected claims which the Examiner has indicated is patentably distinct.

Applicants believe that no extension of time is required. However, this conditional petition is being made to provide for the possibility that Applicants have inadvertently overlooked the need for a petition for extension of time. The Commissioner is hereby authorized to charge any additional fees associated with this

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communication or credit any overpayment to Deposit Account No. 50-0417. A duplicate copy of this Response is enclosed for accounting purposes.

Respectfully submitted,

McDERMOTT, WILL & EMERY

Date: _____

6/2/03

By: _____

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